

Notice of References Cited	Application/Control No. 10/822,820	Applicant(s)/Patent Under Reexamination NAKAZAWA ET AL.	
	Examiner Granvill D Lee, Jr	Art Unit 2825	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-5,804,473	09-1998	Takizawa, Yutaka	438/166
	B	US-5,994,172	11-1999	Ohtani et al.	438/151
	C	US-6,413,805	07-2002	Zhang et al.	438/166
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Schwartz et al. "Electrical properties of chemically derived (Pb,Lu)TiO ₃ thin films" Applications of Ferroelectrics, 1990., IEEE 7th International Symposium 6-8 June, 1990, pg. 254-257.
	V	Kakkad et al. "Crystallized Si films by low-temperature rapid thermal annealing of amorphous silicon" J. Appl. Phys. 65 no. 5 1 March 1989 pg. 2069-2072.
	W	Dausch et al. "Antiferroelectric/ferroelectric composite thin films" Applications of Ferroelectrics, 1994.ISAF '94., Proceedings of the Ninth IEEE International Symposium on , 7-10 Aug. 1994 Pages:701 - 704.
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.